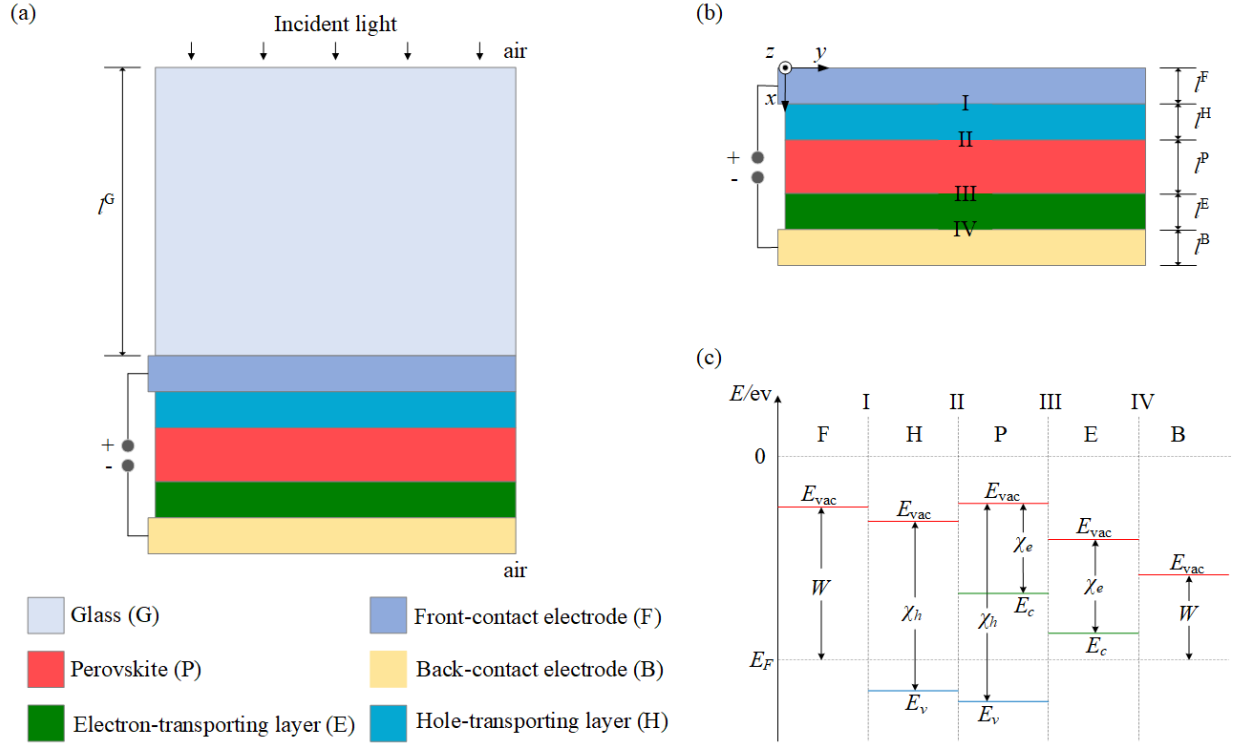


## Explanations on the input and output data

For training of neural network for perovskite solar cells



**Figure 1:** Schematics of (a) a p-i-n perovskite solar cell; (b) the five layers without glass in the perovskite solar cell; and (c) the corresponding energy band diagram.

**Table 1:** Table headers in the data for training, their corresponding symbols, meanings and units.

Table headers in data (.txt) file	Symbols	Explanations	Units
<i>*Inputs</i>			
LH	$l^H$	H layer thickness	nm
LP	$l^P$	P layer thickness	nm
LE	$l^E$	E layer thickness	nm
muHh	$\mu_h^H$	Hole mobility in H	$\text{m}^2 \text{V}^{-1} \text{s}^{-1}$
muPh	$\mu_h^P$	Hole mobility in P	$\text{m}^2 \text{V}^{-1} \text{s}^{-1}$
muPe	$\mu_e^P$	Electron mobility in P	$\text{m}^2 \text{V}^{-1} \text{s}^{-1}$
muEe	$\mu_e^E$	Electron mobility in E	$\text{m}^2 \text{V}^{-1} \text{s}^{-1}$
NvH	$N_v^H$	Valance band density of state in H	$\text{m}^{-3}$
NcH	$N_c^H$	Conduction band density of state in H	$\text{m}^{-3}$
NvE	$N_v^E$	Valance band density of state in E	$\text{m}^{-3}$
NcE	$N_c^E$	Conduction band density of state in E	$\text{m}^{-3}$
NvP	$N_v^P$	Valance band density of state in P	$\text{m}^{-3}$
NcP	$N_c^P$	Conduction band density of state in P	$\text{m}^{-3}$
chiHh	$\chi_h^H$	Hole ionization potential in H	eV
chiHe	$\chi_e^H$	Electron affinity in H	eV
chiPh	$\chi_h^P$	Hole ionization potential in P	eV

chiPe	$\chi_e^P$	Electron affinity in P	eV
chiEh	$\chi_h^E$	Hole ionization potential in E	eV
chiEe	$\chi_e^E$	Electron affinity in E	eV
Wlm	$W_B$	Work function of B	eV
Whm	$W_F$	Work function of F	eV
epsH	$\epsilon^H$	Relative permittivity in H	-
epsP	$\epsilon^P$	Relative permittivity in P	-
epsE	$\epsilon^E$	Relative permittivity in E	-
Gavg	$G_{avg}$	Average charge carrier generation rate in P	$m^{-3} s^{-1}$
Aug	$A_{(e,h)}$	Auger recombination coefficient in P	$m^6 s^{-1}$
Brad	$B_{rad}$	Radiative recombination coefficient in P	$m^3 s^{-1}$
Taue	$\tau_e$	Electron lifetime in P	s
Tauh	$\tau_h$	Hole lifetime in P	s
vII	$v_{II}$	Interface recombination velocity at II	$m^4 s^{-1}$
vIII	$v_{III}$	Interface recombination velocity at III	$m^4 s^{-1}$
<i>*Outputs</i>			
isc	$i_{sc}$	Short-circuit current density	$A m^{-1}$
Voc	$V_{oc}$	Open-circuit voltage	V
FF	$\mathfrak{F}$	Fill factor	-
PCE	$\eta$	Power conversion efficiency	-
i_Rad_MPP	$i_{rad}^{MPP}$	Loss due to radiative recombination at maximum power point	$A m^{-1}$
i_Rsrh_MPP	$i_{srh}^{MPP}$	Loss due to Shockley-Read-Hall recombination at maximum power point	$A m^{-1}$
i_Raug_MPP	$i_{aug}^{MPP}$	Loss due to Auger recombination at maximum power point	$A m^{-1}$
i_RII_MPP	$i_{II}^{MPP}$	Loss due to interface recombination at II at maximum power point	$A m^{-1}$
i_RIII_MPP	$i_{III}^{MPP}$	Loss due to interface recombination at III at maximum power point	$A m^{-1}$
i_Rrad_OC	$i_{rad}^{OC}$	Loss due to radiative recombination at open circuit	$A m^{-1}$
i_Rsrh_OC	$i_{srh}^{OC}$	Loss due to Shockley-Read-Hall recombination at open circuit	$A m^{-1}$
i_Raug_OC	$i_{aug}^{OC}$	Loss due to Auger recombination at open circuit	$A m^{-1}$
i_RII_OC	$i_{II}^{OC}$	Loss due to interface recombination at II at open circuit	$A m^{-1}$
i_RIII_OC	$i_{III}^{OC}$	Loss due to interface recombination at III at open circuit	$A m^{-1}$
i_Rrad_SC	$i_{rad}^{SC}$	Loss due to radiative recombination at short circuit	$A m^{-1}$
i_Rsrh_SC	$i_{srh}^{SC}$	Loss due to Shockley-Read-Hall recombination at short circuit	$A m^{-1}$
i_Raug_SC	$i_{aug}^{SC}$	Loss due to Auger recombination at short circuit	$A m^{-1}$
i_RII_SC	$i_{II}^{SC}$	Loss due to interface recombination at II at short circuit	$A m^{-1}$
i_RIII_SC	$i_{III}^{SC}$	Loss due to interface recombination at III at short circuit	$A m^{-1}$

\*The inputs and outputs can be selective. They are also not fixed; for examples:

- 1) Outputs can be either the cell performances, namely the isc, Voc, FF and PCE, or the recombination losses
- 2) Information from i-V curves can be the inputs as well?